



NTE5906, NTE5907, NTE5980 thru NTE6005 Silicon Power Rectifier Diode, 40 Amp, DO5

Features:

- High Surge Current Capability
- High Voltage Available
- Designed for a Wide Range of Applications
- Available in Anode-to-Case or Cathode-to-Case Style

Ratings and Characteristics:

Average Forward Current ($T_C = +140^{\circ}\text{C Max}$), $I_{F(AV)}$ 40A

Maximum Forward Surge Current, I_{FSM}

 50Hz 480A

 60Hz 500A

Fusing Current, I^2t

 50Hz 1150A²s

 60Hz 1050A²s

Fusing Current, $I^2\sqrt{t}$ 16000A²√s

Maximum Reverse Recovery Voltage Range, V_{RRM} 50 to 1600V

Voltage Ratings:

NTE Type Number		V_{RRM} -Max Repetitive Peak Reverse Volt. (V)	V_{RSM} -Max Non-Repertitive Peak Reverse Voltage (V) $t_p < 5\text{ms}$	V_R -Max. Direct Reverse Voltage (V)	$V_{R(SR)}$ Minimum Avalanche Voltage (V)	I_{RM} -Max Reverse Current Rated V_{RRM} (mA)
Cathode to Case	Anode to Case	$T_J = -65^{\circ}\text{ to }+150^{\circ}\text{C}$	$T_J = +25^{\circ}\text{ to }+150^{\circ}\text{C}$	$T_J = -65^{\circ}\text{ to }+150^{\circ}\text{C}$	$T_J = +25^{\circ}\text{C}$	$T_J = +150^{\circ}\text{C}$
5980	5981	50	100	50	–	15
5982	5983	100	200	100	–	15
5986	5987	200	300	200	–	15
5988	5989	300	450	300	–	15
5990	5991	400	500	400	500	15
5992	5993	500	600	500	600	9
5994	5995	600	720	600	725	9
5998	5999	800	960	800	960	9
6002	6003	1000	1200	1000	1150	9
5906	5907	1200	1400	1200	1350	9
6004	6005	1600	1700	1600	1700	9

Electrical Specifications:

Parameter	Symbol	Test Conditions		Rating	Unit
Maximum Average Forward Current	I _{F (AV)}	180° sinusoidal condition, T _C = +140°C Max		40	A
Maximum Peak One–Cycle Non–Repetitive Surge Current	I _{FSM}	Half cycle 50Hz sine wave or 8ms rectangular pulse	Following any rated load condition and with rated V _{RRM} applied	480	A
		Half cycle 60Hz sine wave at 5ms rectangular pulse		500	A
		Half cycle 50Hz sine wave or 6ms rectangular pulse	Following any rated load condition and with V _{RRM} applied following surge = 0	570	A
		Half cycle 60Hz sine wave at 3ms rectangular pulse		586	A
Maximum I ² t for Fusing	I ² t	t = 10ms	With rated V _{RRM} ap- plied following surge	1150	A ² s
		t = 8.3ms		1050	A ² s
Maximum I ² t for Individual Device Fusing		t = 10ms	With V _{RRM} = 0 fol- lowing surge	1600	A ² s
		t = 8.3ms		1450	A ² s
Maximum I ² √t	I ² √t	t = 0.1 to 10ms, V _{RRM} = 0 following surge		16000	A ² √t
Maximum Peak Forward Voltage	V _{FM}	I _{F (AV)} = 40A (125 peak), T _J = +25°C		1.30	V
Maximum Value of Threshold Voltage	V _{M (TO)}	T _J = +100°C		0.69	V
Maximum Value of Forward Slope Resistance	r _t	T _J = +100°C		3.79	mΩ

Thermal-Mechanical Specifications:

Parameter	Symbol	Test Conditions	Rating	Unit
Maximum Operation Junction Temperature	T_J		-65 to + 190	$^{\circ}C$
Maximum Storage Temperature	T_{stg}		-65 to + 190	$^{\circ}C$
Maximum Internal Thermal Resistance Junction-to-Case	R_{thJC}	DC operation	1.00	K/W
Thermal Resistance, Case-to-Sink	R_{thCS}	Mounting surface flat, smooth and greased	0.25	K/W
Mounting Torque	T	Non-lubricated threads	2.3 – 3.4 (20 – 30)	$m\bullet N$ ($in\bullet lb$)
Approximate Weight	wt		17 (0.8)	g (oz)

